

The 4h EUV-FEL Workshop
Akihabara UDX, Tokyo,
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Demonstration of high-repetition FEL using cERL and beyond EUV-FEL

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- Why is Energy Recovery required?
- Project of IR-FEL based on the cERL
 - Demonstration of high-repetition FEL -
- Is it possible to obtain a wavelength of several nm from EUV-FEL?
- Summary

Part 1:

Why is Energy Recovery required?

Efficiency of FEL

- Assuming this square area is the power of the electron beam, how much area is converted to light by FEL?

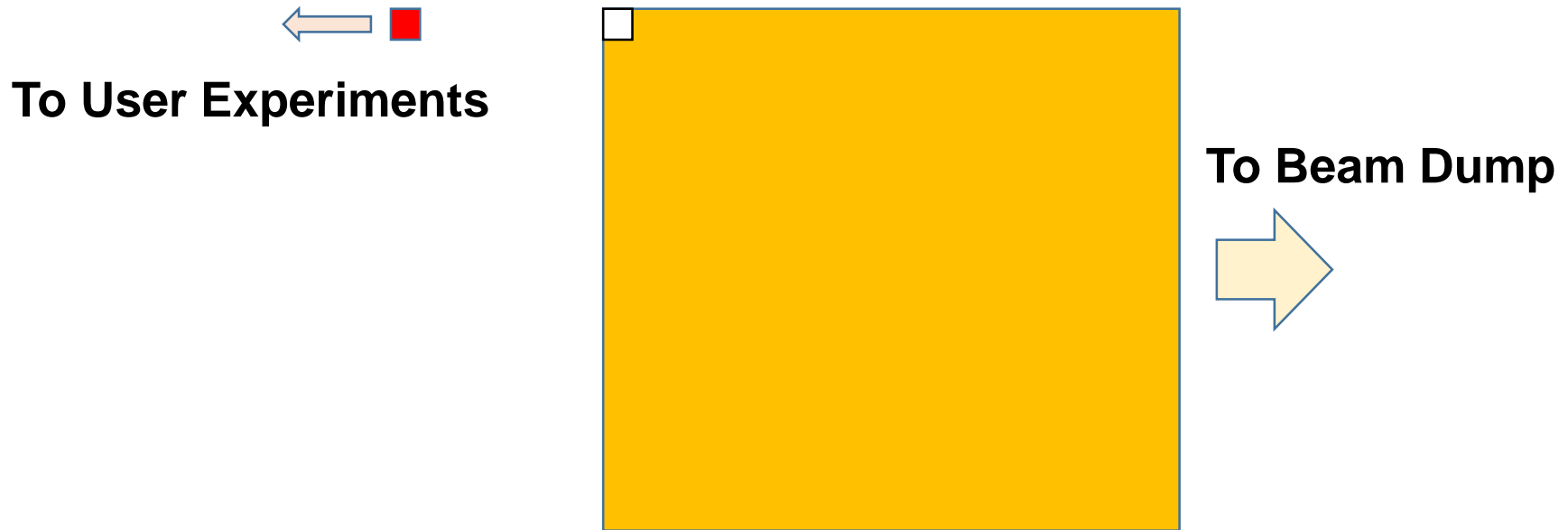
Maybe ...
this red square



- FEL conversion efficiency is $\sim 10^{-2}$ in the infrared region and 10^{-3} to 10^{-4} in the EUV/X-ray region

Efficiency of FEL

- Assuming this square area is the power of the electron beam, how much area is converted to light by FEL?

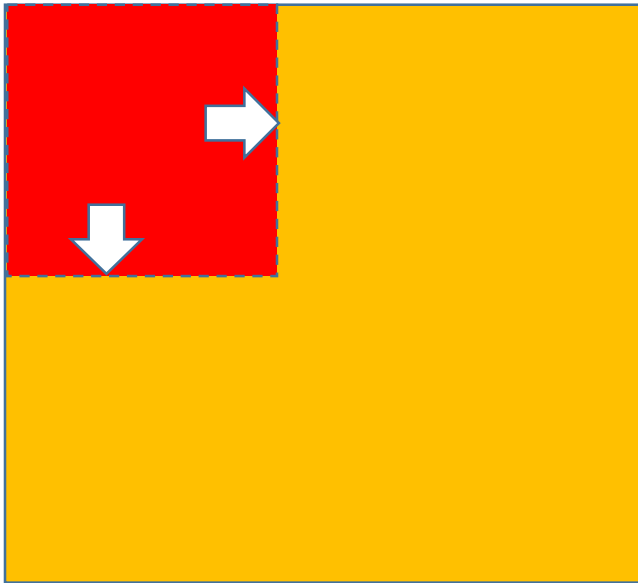


- Low conversion efficiency of FEL is not a serious problem for academic use.
- However, for industrial use ... we need improvement!

To make the efficiency better

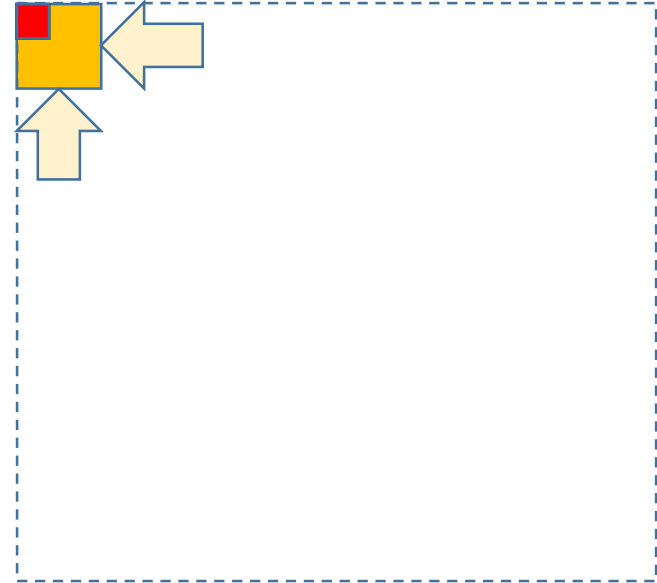
- There are 2 ways to improve conversion efficiency

(1) Increase efficiency itself



Tapered FEL, TESSA*, ...

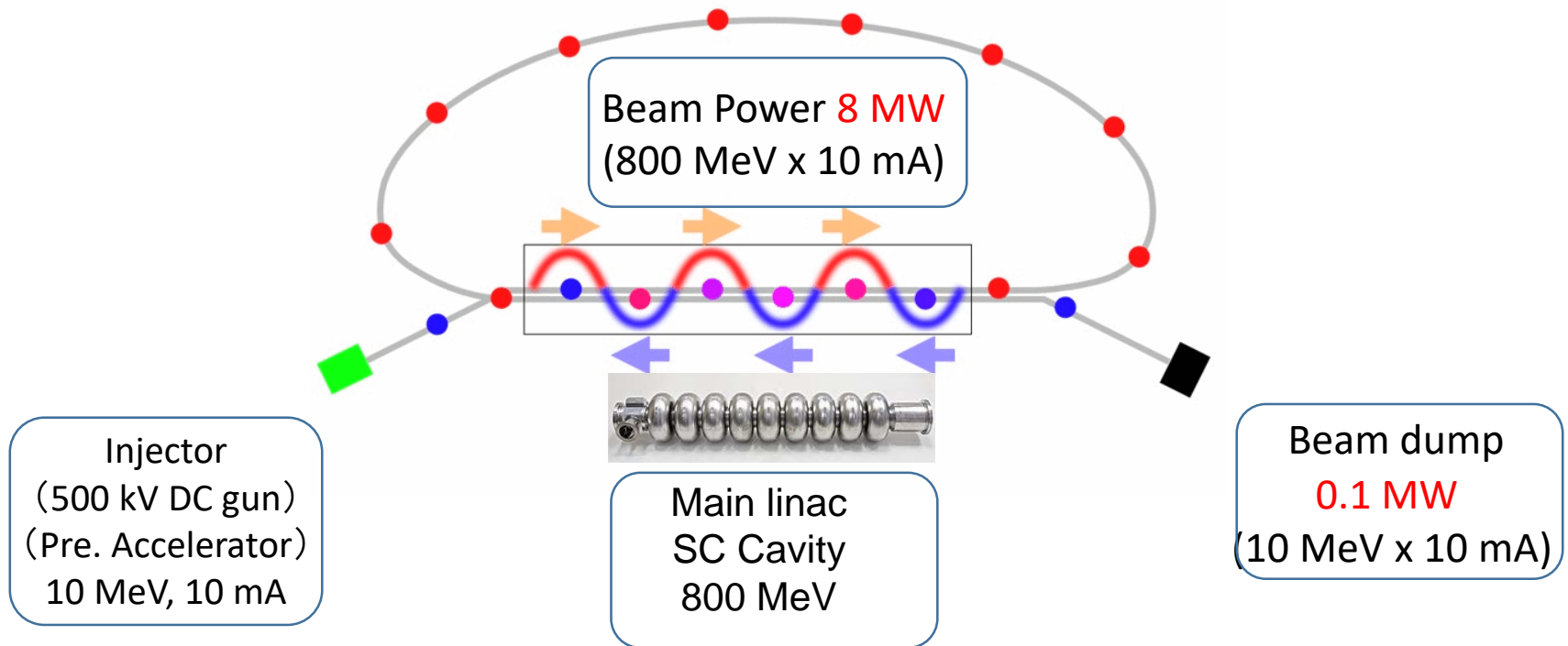
(2) Reduce dump power



Energy Recovery

Energy Recovery Linac

Energy exchanged between fresh bunches (from injector) and old bunches (from circulation) in the main SC Cavities.



- Increase average beam power
- Reduce dump power (small radiation)

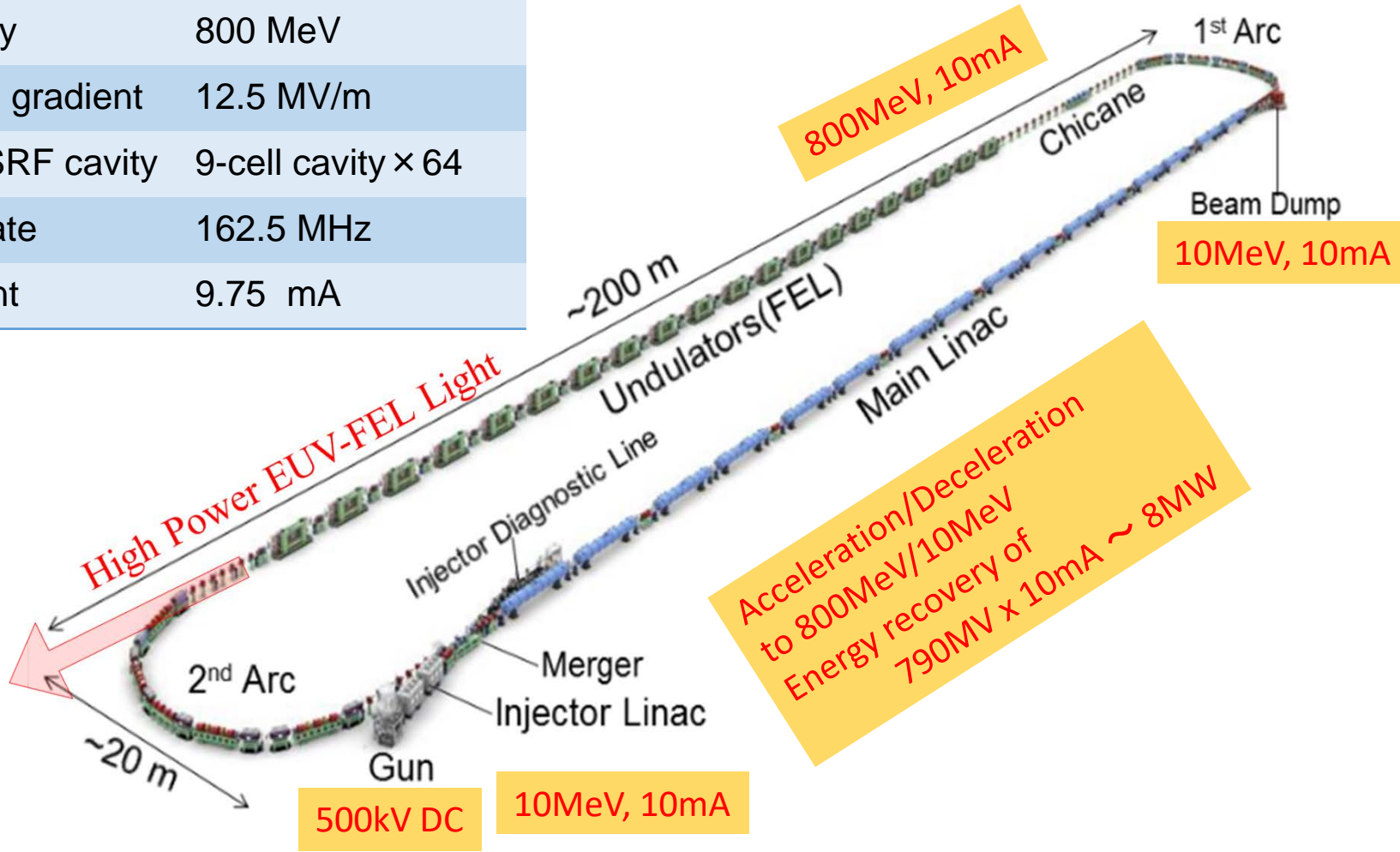
EUV/X-Ray FELs

	LCLS	SACLA	FLASH	Euro-XFEL	LCLS II	EUV-FEL
Type	Normal conducting		Super conducting			
Configuration	Linac		Linac			ERL
Operation Mode	Pulse		Long-pulse		CW	
Country	US	Japan	Germany	EU	US	---
Repetition rate (pulse/sec)	120	60	<5000	<27000	1M	162.5M
Beam energy (GeV)	14.3	6~8	1.25	17.5	4	0.8
Wavelength (nm)	0.15	0.08	4.2-52	0.05	~0.3	13.5
FEL Pulse energy (mJ)	~10	~10	<0.5	~10	~1	~0.1
Average FEL power (W)	~1	~1	<0.6	~100	~1k	>10k
Beam dump power (W)	~1.5k	~0.5k	~6k	~0.5M	~1M	~0.1M
FEL / Dump (%)	0.07	0.2	0.01	0.02	0.1	10
Status	Operation 2009	Operation 2011	Operation 2004	Operation 2017	Construction 2020	Planning

ERL helps to make high-power CW FEL and reduce the beam dump power.

Prototype design of the EUV-FEL

Parameter	Specification
Wavelength	13.5 nm
Output power	> 10 kW
Bunch charge	60 pC
Beam energy	800 MeV
Accelerating gradient	12.5 MV/m
Number of SRF cavity	9-cell cavity × 64
Repetition rate	162.5 MHz
Beam current	9.75 mA



10kW FEL output

500kV DC

10MeV, 10mA

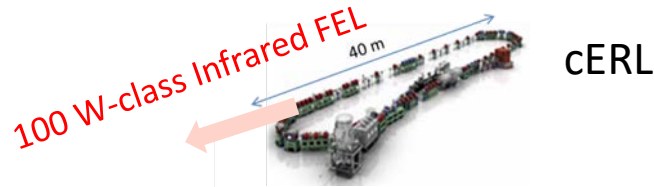
800MeV, 10mA

10MeV, 10mA

Acceleration/Deceleration to 800MeV/10MeV
Energy recovery of 790MV x 10mA ~ 8MW

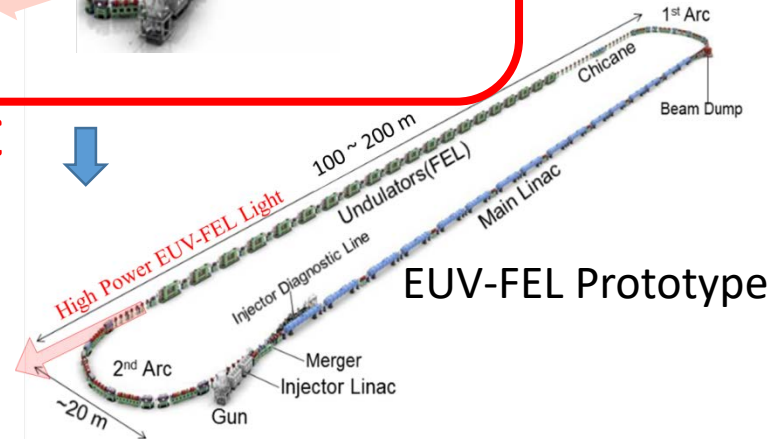
Staging to realize the EUV-FEL light source

1st stage:
Development of the
feasible technologies

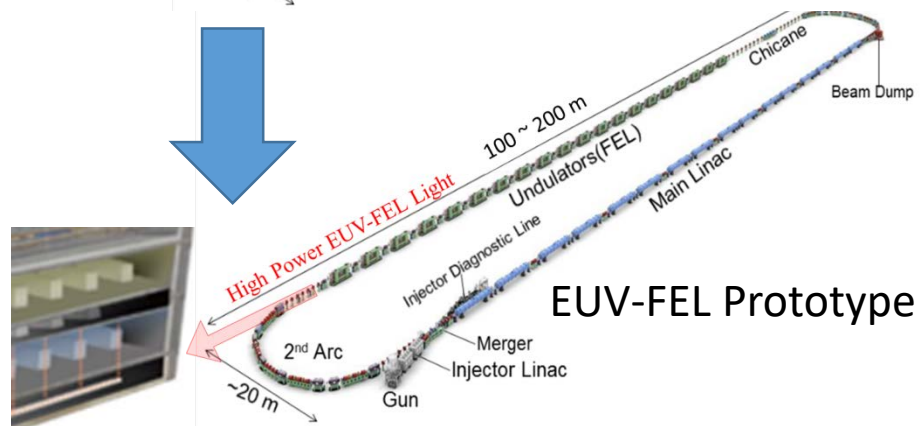


Upgrade plan of cERL for the PoC

2nd stage Phase 1:
Establishment of the EUV-FEL
Lithography system



2nd stage Phase 2:
International Development
Center on the processing of
EUV-FEL lithography



Clean room with EUV exposure system

IR-FEL project as a PoC is important to realize
the EUV-FEL light source for future EUV Lithography.

Part 2:

**Project of IR-FEL based on the cERL
- Demonstration of high-repetition FEL -**

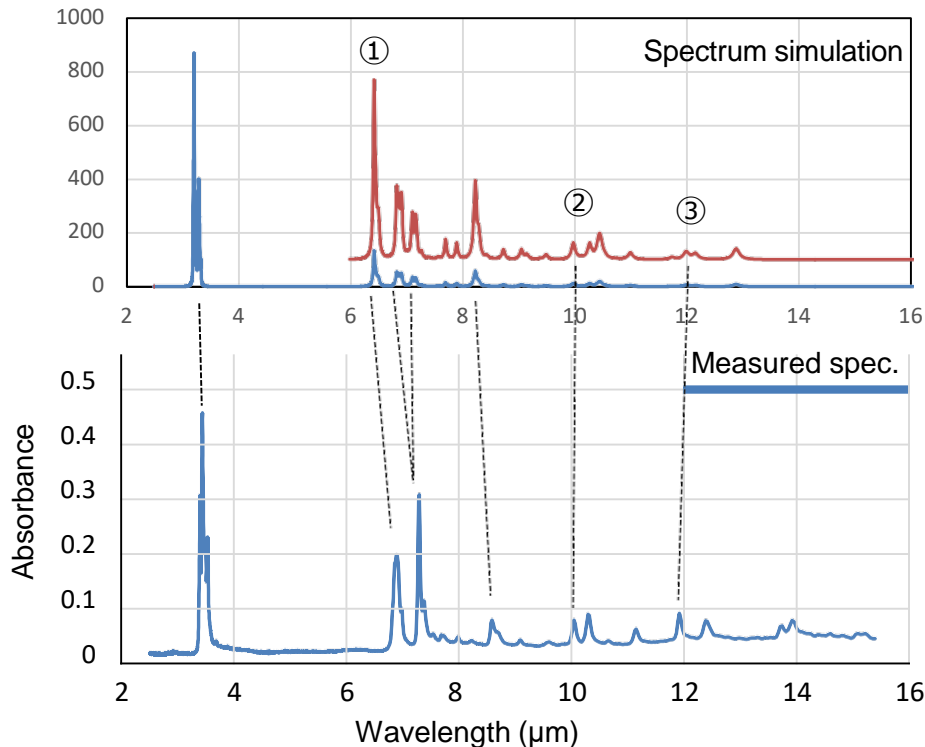
Background of IR-FEL Project (1)

Organic materials (Resin, Engineering plastic) : light-weight, low-cost, high-functional
Recently, the use of organic materials has been increasing.

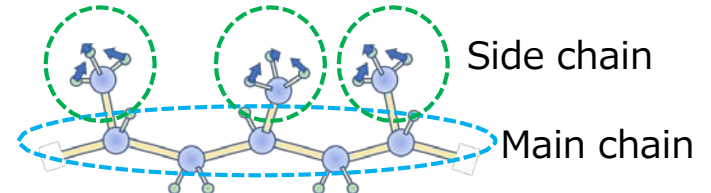
Processing methods : Machining, Molding, Laser processing (CO₂, Fiber)

These organic materials have vibration absorption in the mid-infrared region

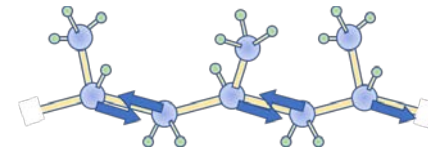
Absorption spectrum of polypropylene



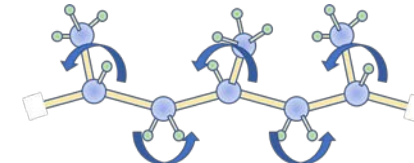
Peak①: δ declination of side chain methyl group



Peak②: Stretch vibration of main chain C-C bond



Peak③: Twist of main chain C-C bond



Considering the process of cutting the resin, the absorption wavelength of ② and ③ seem to be more suitable than ①,

However, there is no database of easy-to-process wavelengths and required laser power.

Background of IR-FEL Project (2)

Main high-power laser in MIR range is CO₂ laser only

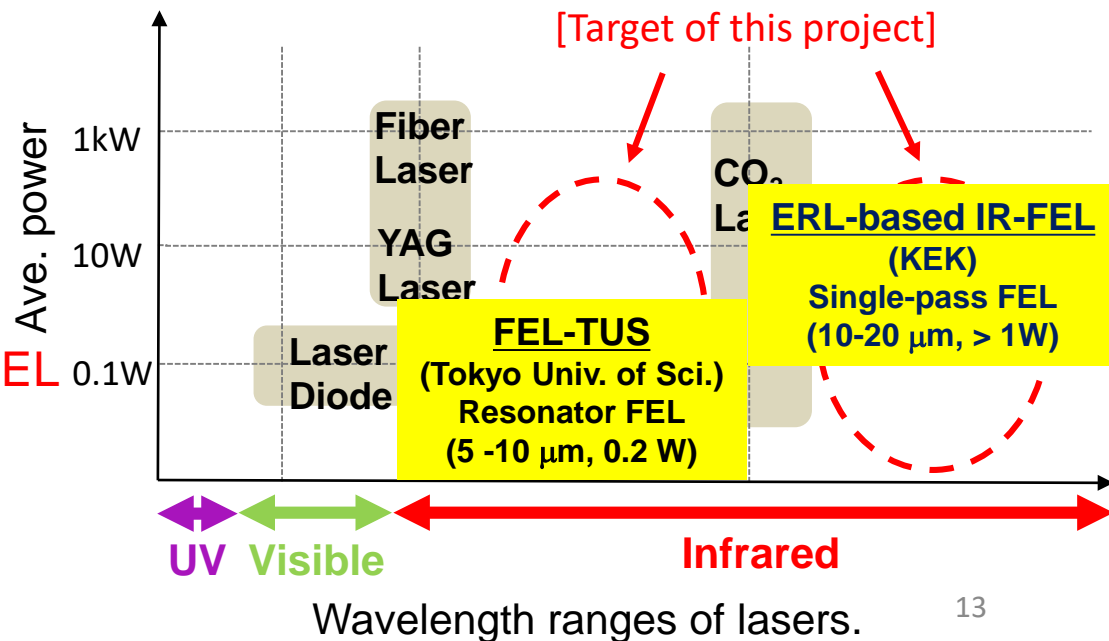
→ Insufficient understanding of basic phenomena required for processing

A tunable high-power laser is required to create a database for processing!

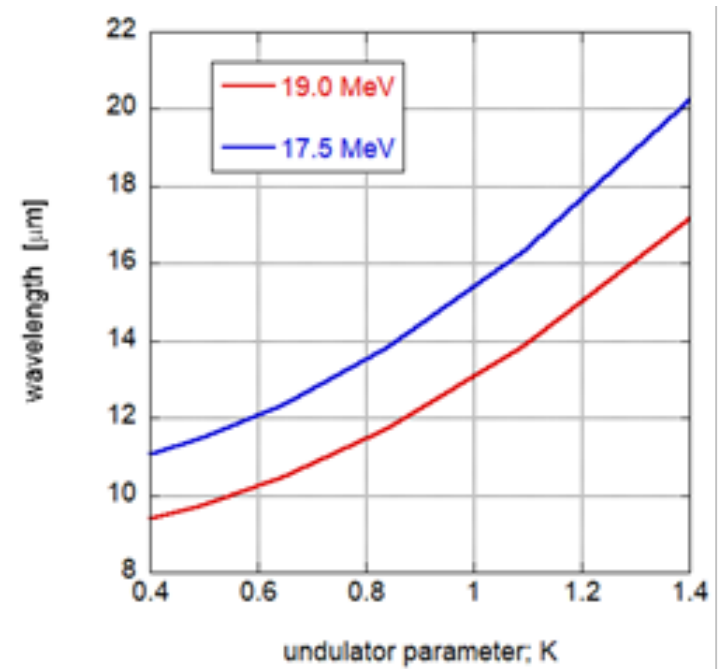
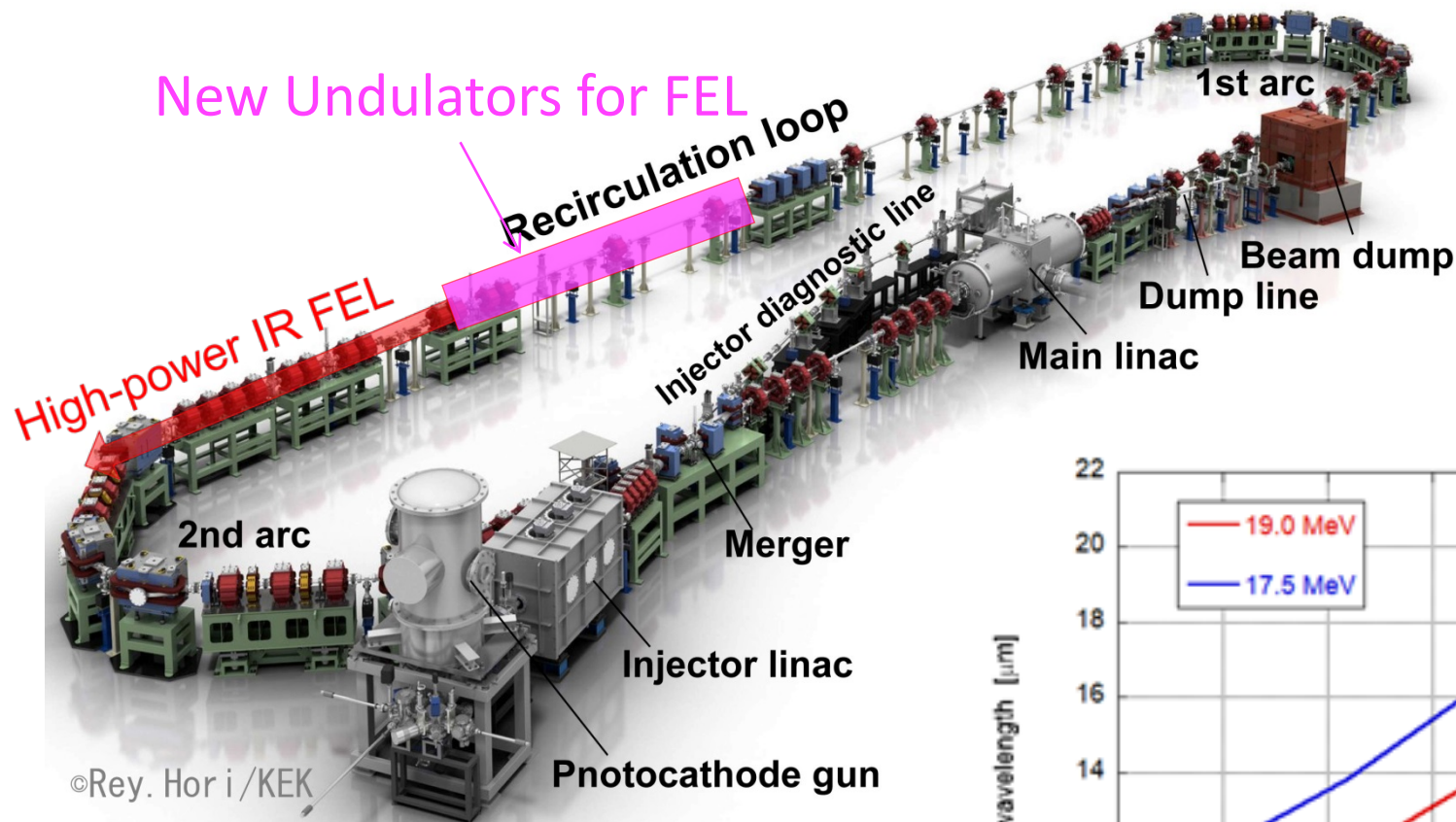
Project theme founded by NEDO (Ministry of Economy, Trade and Industry)
“Development of high-power mid-infrared lasers for high-efficiency laser processing utilizing photo-absorption based on molecular vibrational transitions.”

KEK's mission

1. Development of high-power IR-FEL
2. Creation of processing database
3. Processing demonstration



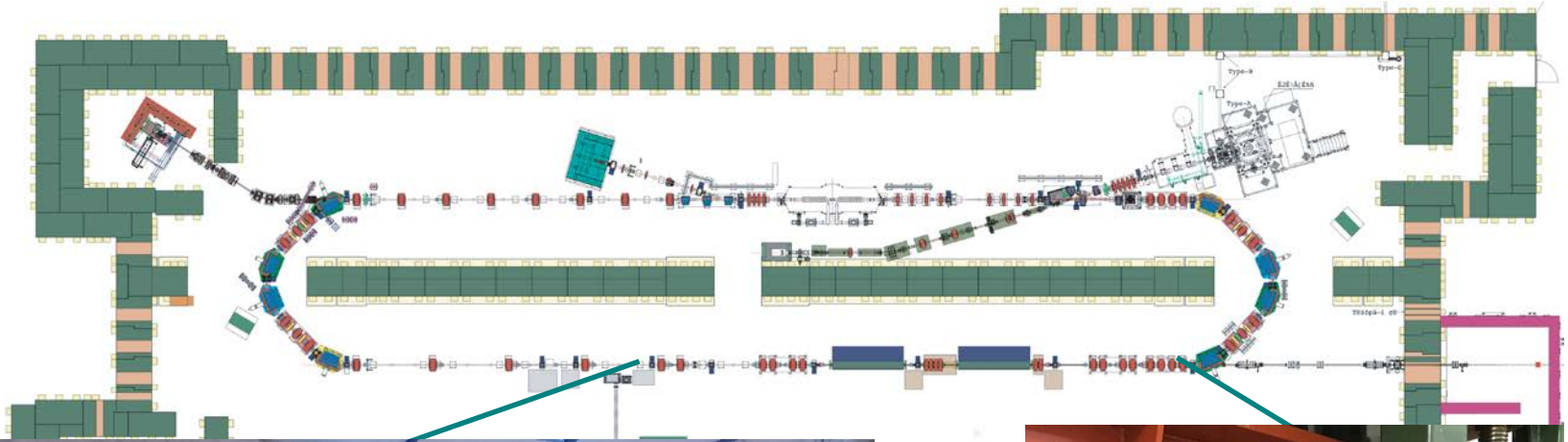
High average power IR-FEL Project



Beam Energy	17.5 - 19.0 MeV
Injector Energy	3.0 - 4.0 MeV
E-Gun Energy	500 keV
Bunch repetition	1.3 GHz → 81.25 MHz
Average current	1 mA (→ 5 mA)
Operation mode	CW or Burst

FEL wavelength

Layout and parameters of IR-FEL



Wiggler

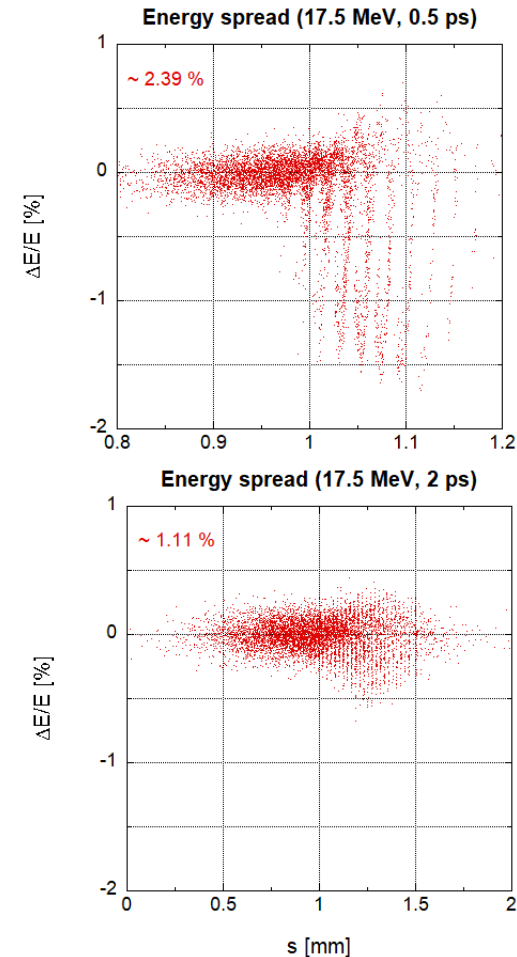
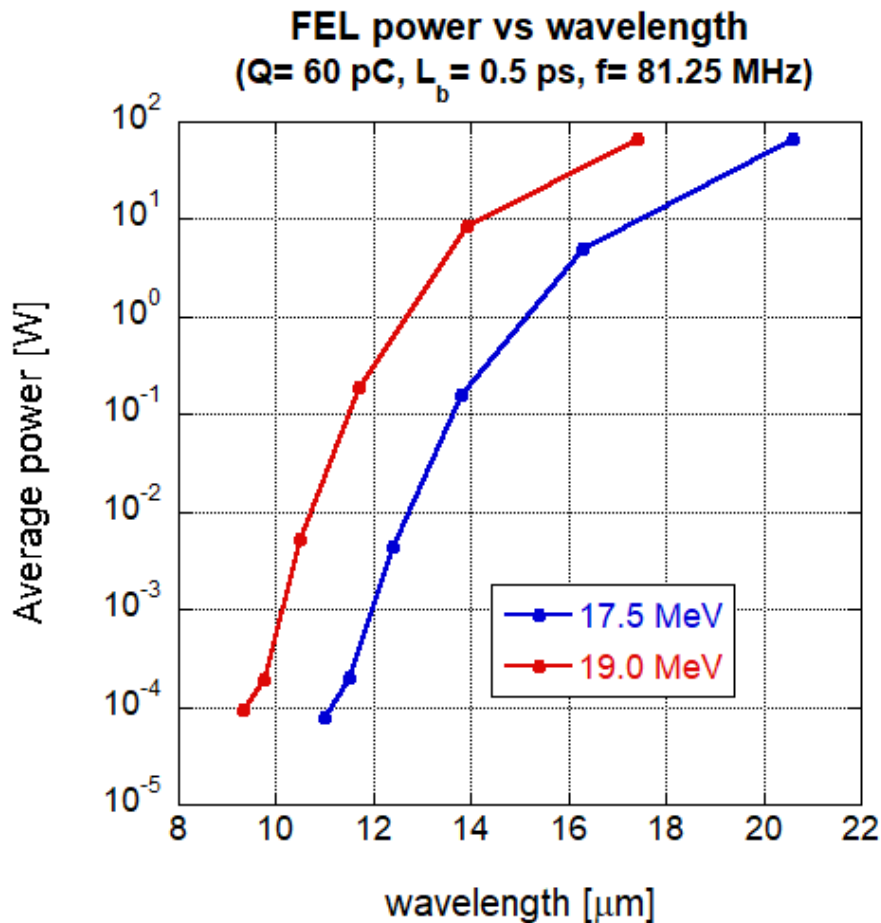
Undulator

Design of undulators.

Ave. Power of IR-FEL and energy spread

By changing the energy, average power exceeding 1 W can be obtained in the range of 13 – 20 μm .

A large density modulation is formed in front of the electronic bunch due to the slippage effect.

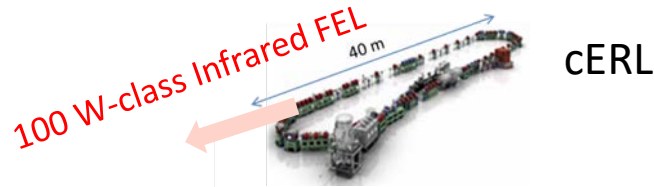


Items to be consider for cERL-FEL from the view points of beam operation

1. Operation of high current beam
 - Average current of 5 mA (10 mA @ EUV-FEL)
 - Bunch charge of 60 pC with low emittances
 - Bunch repetition rate of 81.25 MHz (162.5 MHz @ EUV-FEL)
2. Beam transportation after FEL
 - Large energy spread due to FEL lasing
 - Beam loss in the dispersion sections (dump line, 2nd arc)
3. Bunch compression & decompression
 - Essential to EUV-FELs
 - Increased peak currents for FEL
 - Reduced energy spread after deceleration

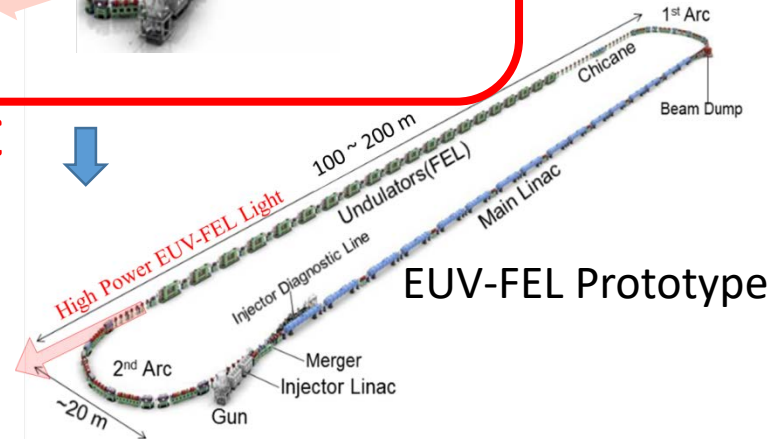
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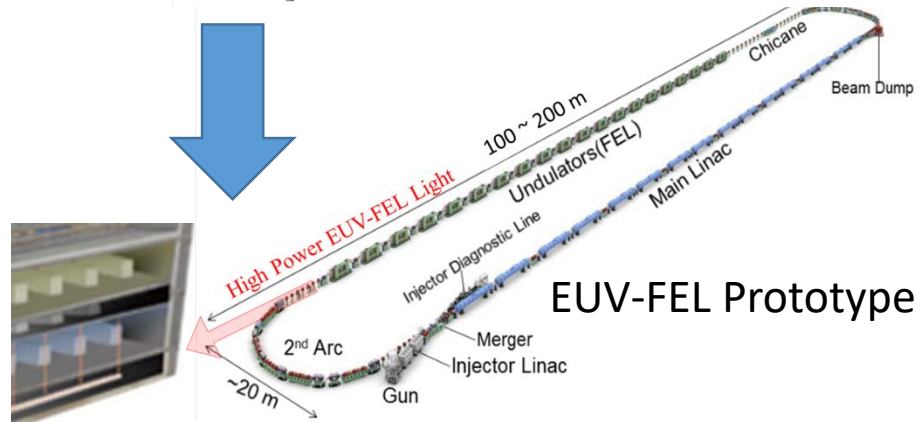


Upgrade plan of cERL for the PoC

2nd stage Phase 1:
Establishment of the EUV-FEL
Lithography system



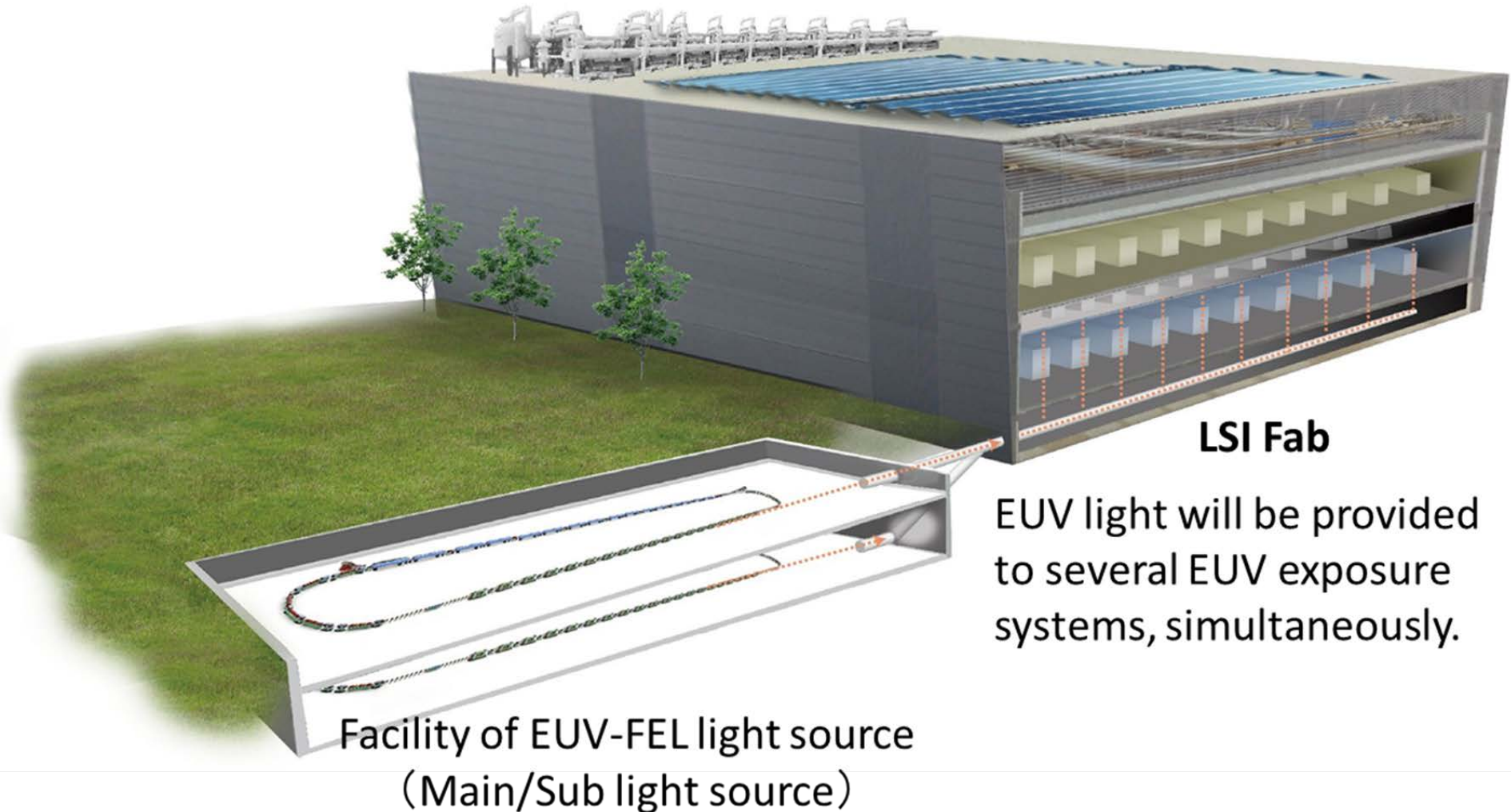
2nd stage Phase 2:
International Development
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Clean room with EUV exposure system

IR-FEL project as a PoC is important to realize
the EUV-FEL light source for future EUV Lithography.

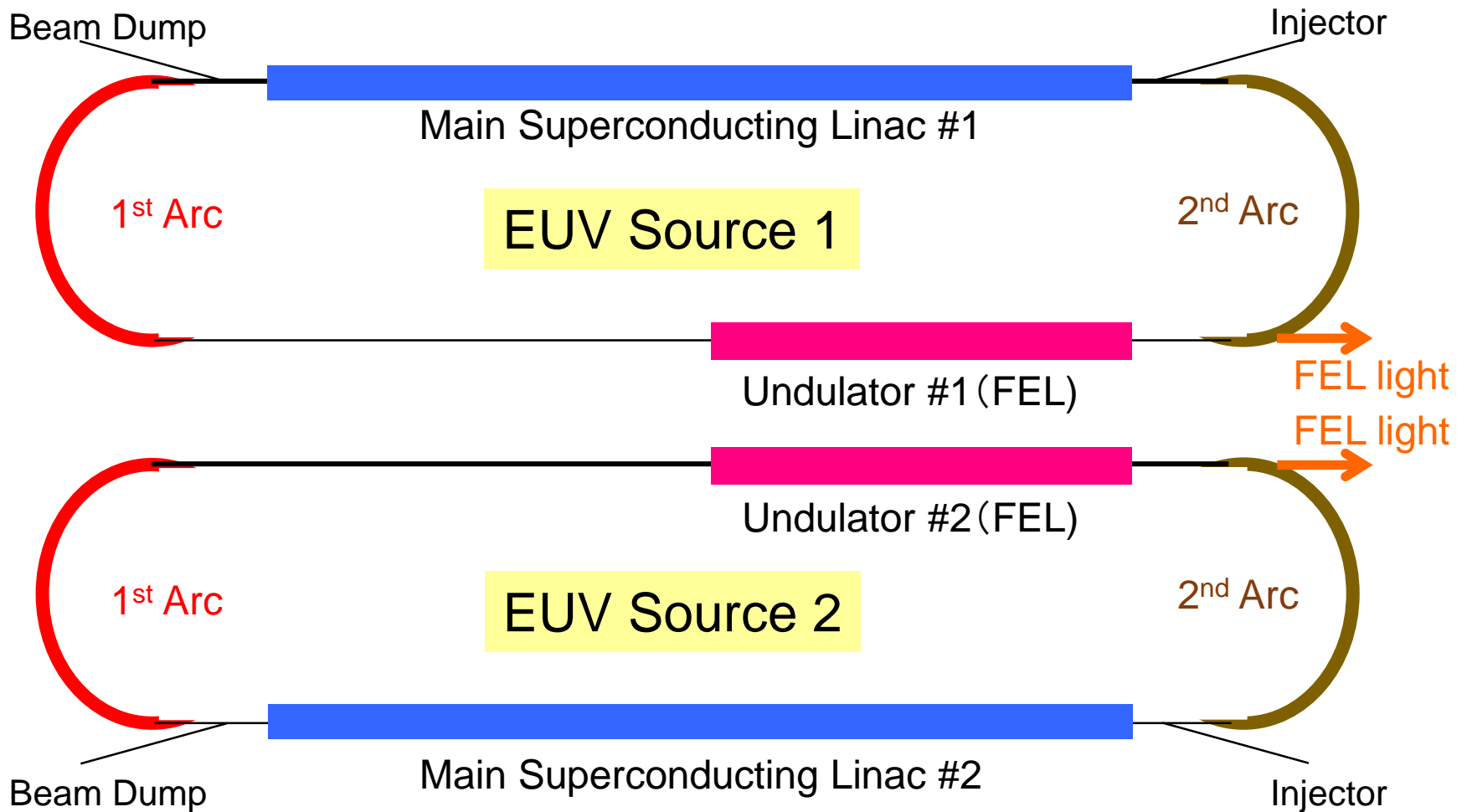
Expected LSI Fab with EUV-FEL



Part 3:

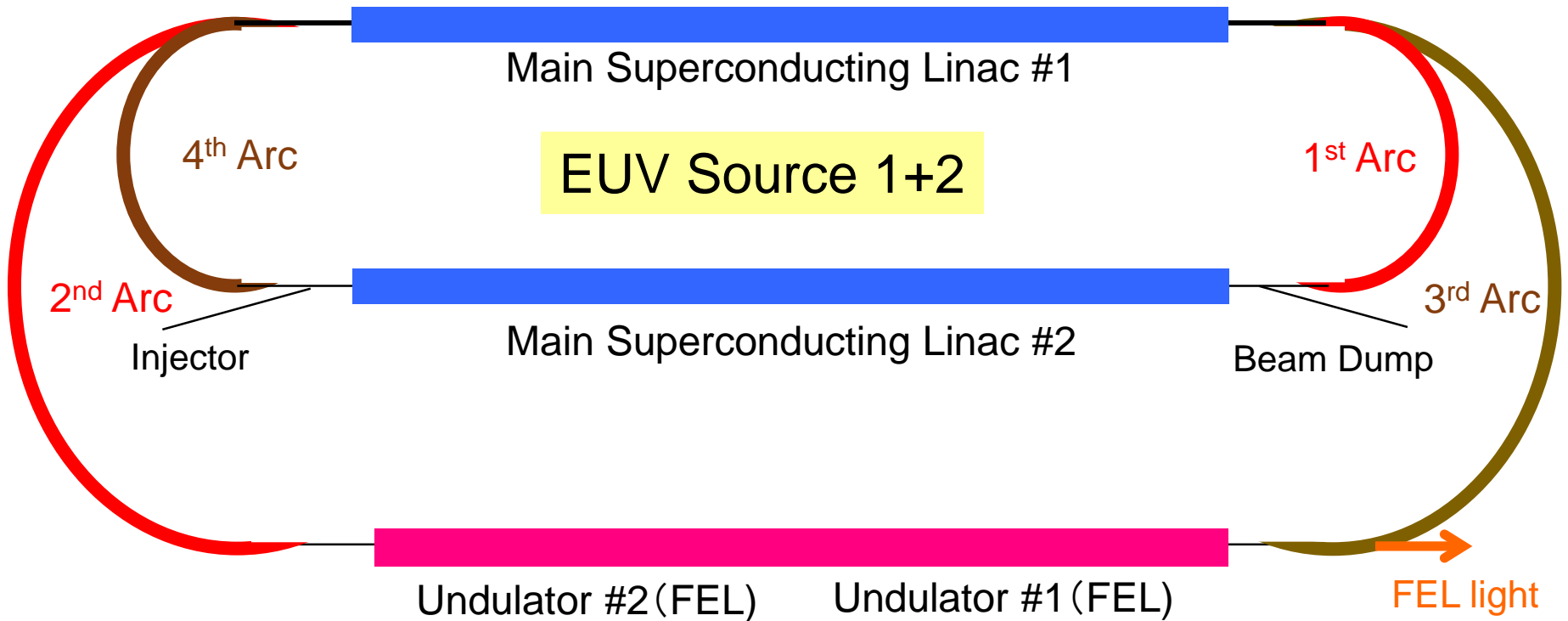
Is it possible to obtain a wavelength of several nm from EUV-FEL?

Redundancy of EUV-FEL (13.5 nm)



FEL output power : 10 kW x 2 (13.5 nm, redundant)

Rearrangement of EUV-FEL (3.4 nm)



FEL output power : ~10 kW (3.4 nm)

SASE-FEL formula (1D model)

- FEL wavelength**

$$\lambda = \frac{\lambda_u}{2\gamma^2} \left(1 + \frac{K^2}{2} \right)$$

$$[JJ] = J_0(\xi) - J_1(\xi)$$

$$\xi = \frac{(K/2)^2}{2(1 + (K/2)^2)}$$

- FEL parameter (1D)**

$$\rho = \frac{1}{\gamma} \left\{ \frac{1}{64\pi^2} \frac{I_P}{I_A} \frac{K^2 \lambda_u^2 [JJ]^2}{\sigma_x \sigma_y} \right\}^{\frac{1}{3}}$$

- Gain Length (1D)**

$$L_{gain} = \lambda_u / 4\sqrt{3}\pi\rho$$

- Saturation Length**

$$L_{sat} \approx 20 \times L_{gain}$$

- FEL power**

$$P_{FEL} = \rho P_{beam} = \rho EI_{beam}$$

	13.5 nm	6.7 nm	3.4 nm
Wavelength	λ	$\lambda/2$	$\lambda/4$
Beam Energy	γ	$\sqrt{2}\gamma$	2γ
FEL Parameter (1D)	ρ	$\rho/\sqrt{2}$	$\rho/2$
Gain Length (1D)	L_{gain}	$\sqrt{2}L_{gain}$	$2L_{gain}$
Saturation Length	L_{sat}	$\sqrt{2}L_{sat}$	$2L_{sat}$
Beam Power	P_{beam}	$\sqrt{2}P_{beam}$	$2P_{beam}$
FEL Power	ρP_{beam}	ρP_{beam}	ρP_{beam}

Issues beyond the EUV-FEL

- **Stochastic effect**
- **Low reflectivity of multilayer mirror**
- **Narrow bandwidth of multilayer mirror**

Issues beyond the EUV-FEL

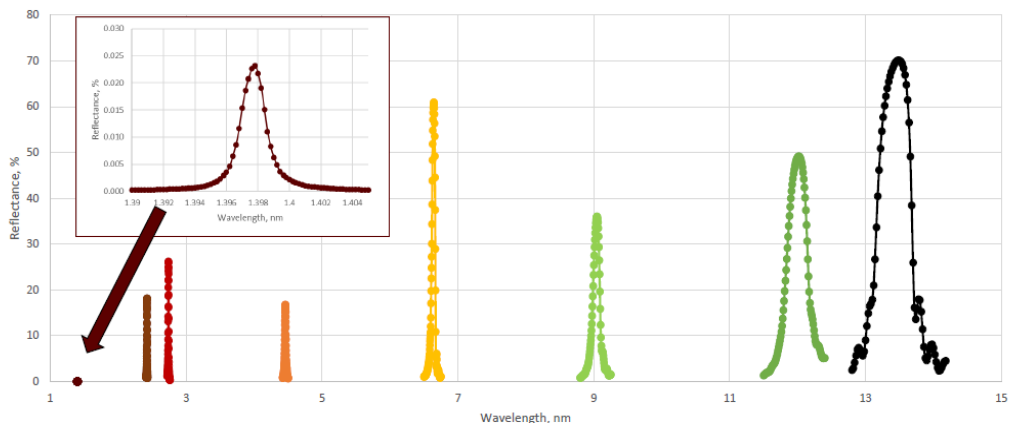
- **Stochastic effect**
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Issues beyond the EUV-FEL

Low reflectivity & Narrow bandwidth of multilayer mirrors were shown at 2018&2019 Source Workshop from optiX fab.

Experimental results

λ , nm	1.4	2.4	2.7	4.4	6.7	9.0	12.0	13.5
R, %	0.02	18.1	26.2	16.8	61.0	36.0	49.2	70.1
FWHM, nm	0.002	0.005	0.008	0.02	0.05	0.11	0.32	0.52



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Prague, Nov. 6, 2018

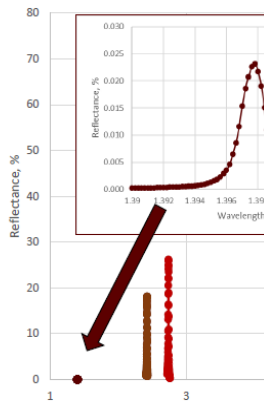
optiXfab.

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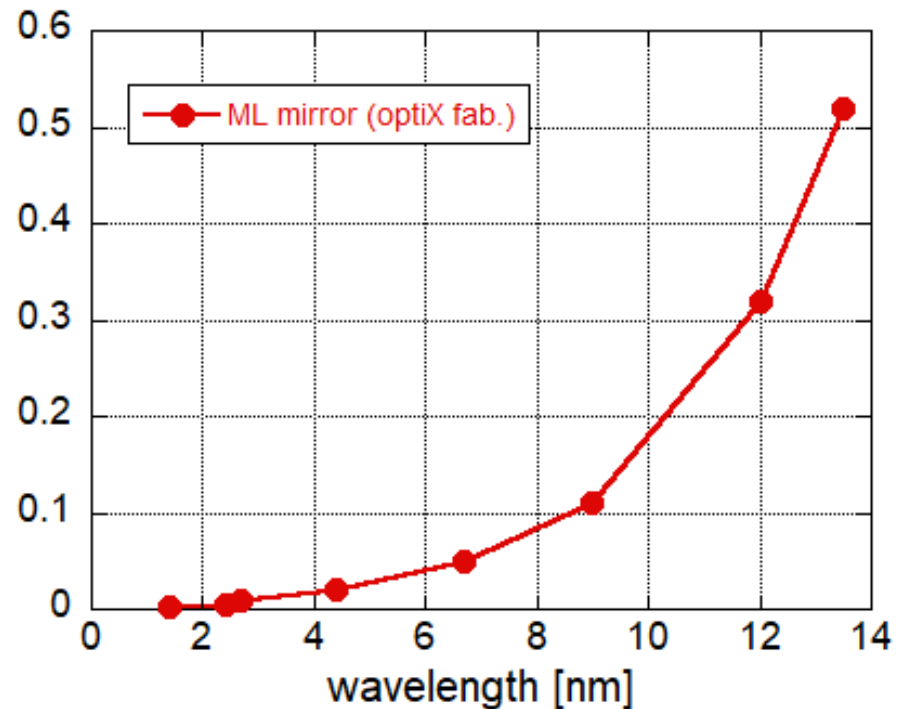
Experimental results

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FWHM, nm	0.00



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Prague, Nov. 6, 2018

bandwidth (FWHM) [nm]

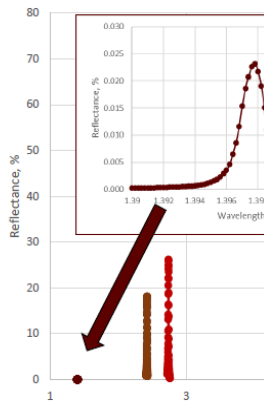


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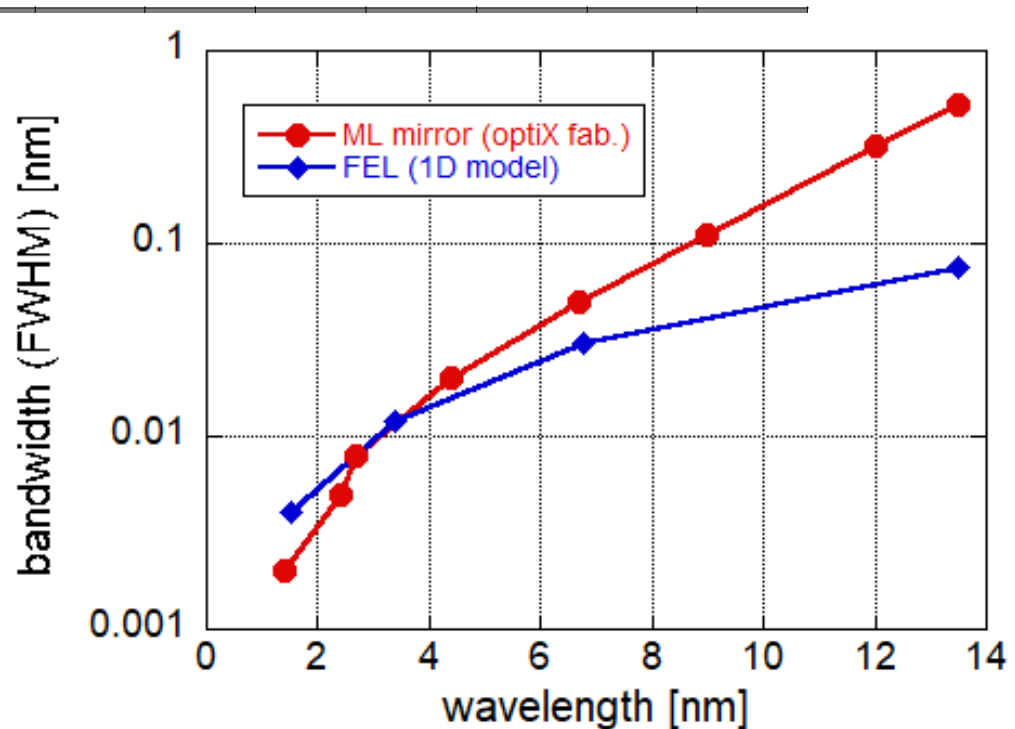
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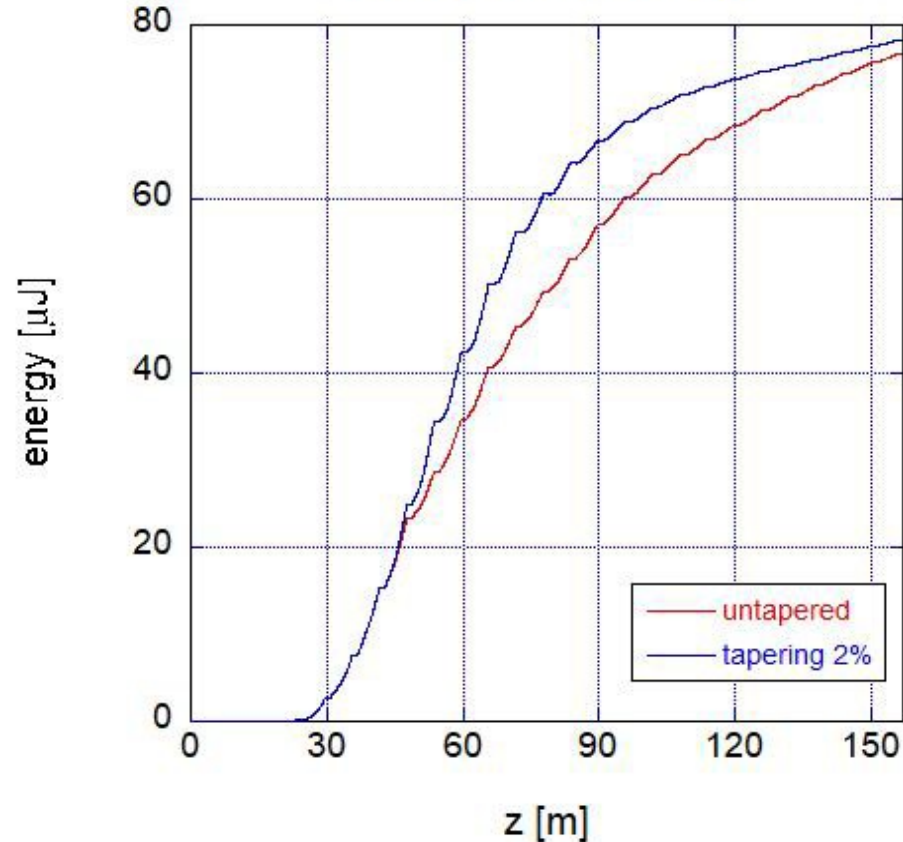


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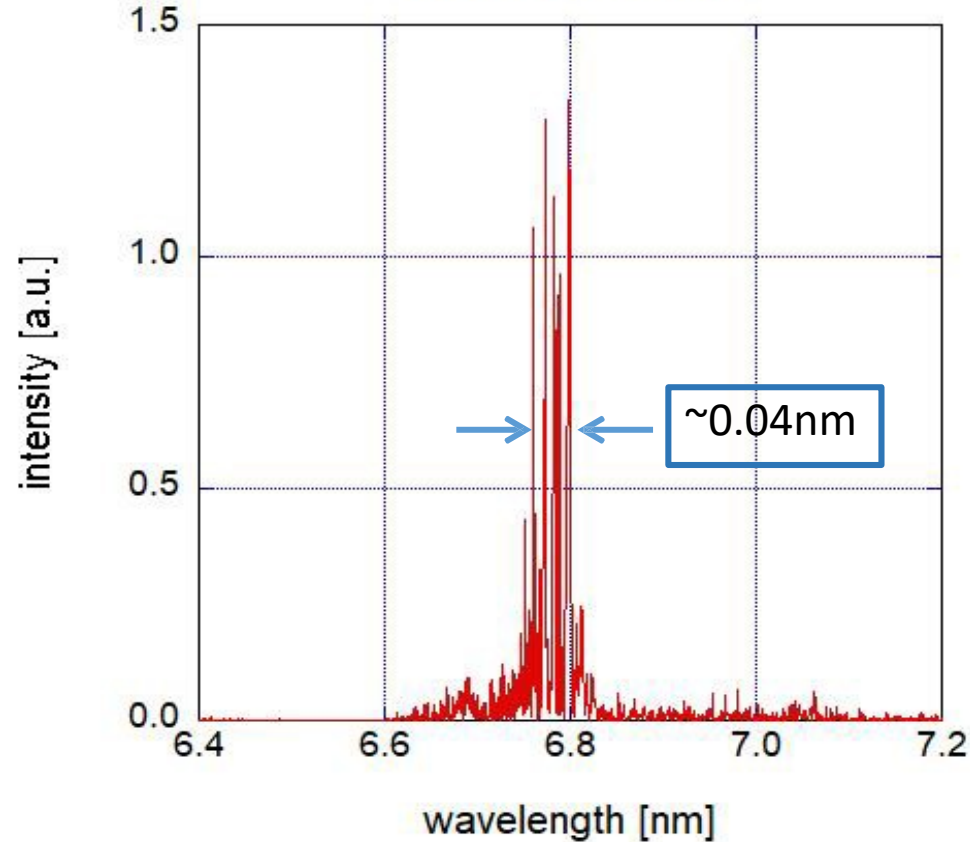


Recent study about the power and spectrum

FEL pulse energy



FEL spectrum



FEL power with 2% tapering:
12.7/25.4 kW @ 9.75/19.5 mA (162.5/325 MHz)

$$\Delta\lambda/\lambda = 6 \times 10^{-3}$$

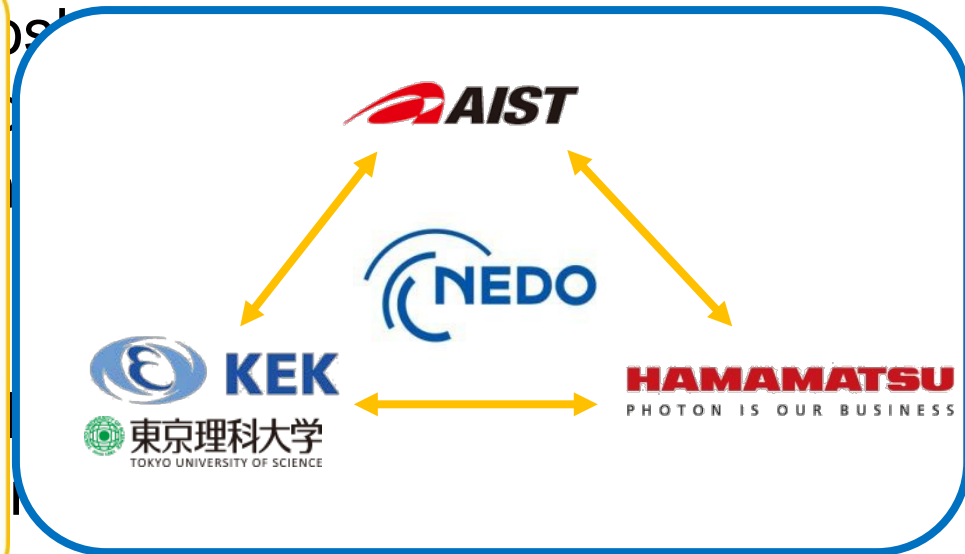
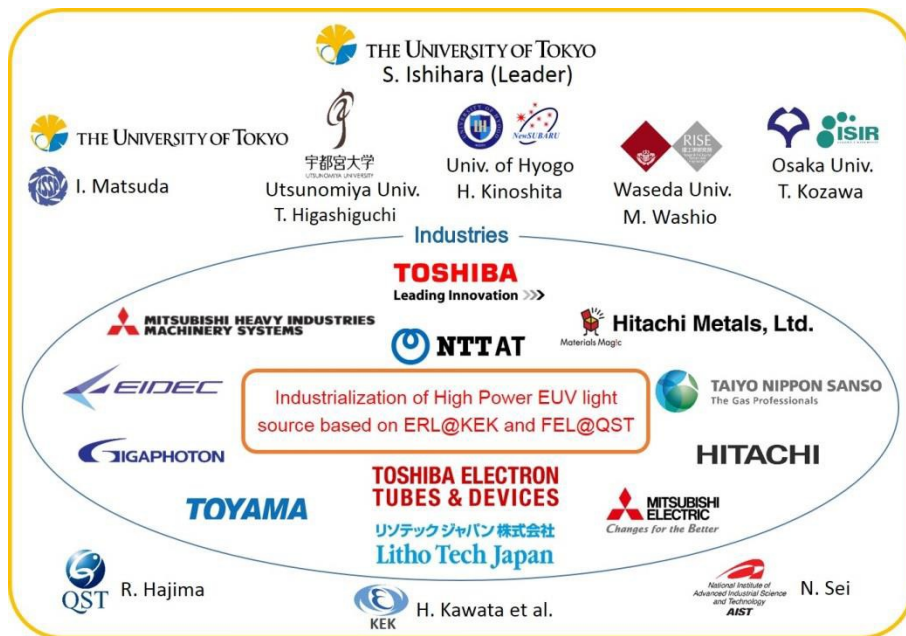
Beam energy : $E = 1131 \text{ MeV} (800 \times \sqrt{2})$,
The other parameters are almost same to these of EUV-FEL

Summary

Summary

- By using ERL technology, FEL can be operated in high repeat rate, and the beam dump power can be reduced.
- KEK will install two undulators in the cERL and develop an infrared FEL with high average power. With the IR-FEL, mid-infrared light can be obtained average power exceeding 1 W in CW operation.
- IR-FEL can demonstrate many of the challenges for the realization of EUV-FEL.
- From the viewpoint of compatibility with the bandwidth of multilayer mirrors, the EUV-FEL's critical wavelength is expected to be about 3.5 nm.
- In the 6.7 nm wavelength range, the FEL spectrum is well within the bandwidth of the multilayer mirror, and an output of 10 kW or more can be expected.

Core members for IR-FEL and Acknowledgement



This presentation is based on results obtained from NEDO project "Development of advanced laser processing with intelligence based high-brightness and high-efficiency laser technologies (TACMI project)."

Thank you for your attention!

